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## **Overview**

This document describes the design example for interfacing Microsemi low-power FPGAs with Mobile SDRAM devices. When used alongside reprogrammable FPGAs such as Microsemi's IGLOO<sup>®</sup> and ProASIC<sup>®</sup>3 product families, this IP makes an ideal solution for high volume, portable applications, such as cell phones, smartphones, PDAs, MP3 players, digital still cameras, video cameras, GPS devices, and portable games.

Associated files for this design example can be downloaded from the Microsemi website: http://soc.microsemi.com/download/rsc/?f=Mobile\_SDRAM\_Interface\_DF

## **Design Description**

The Mobile SDRAM Interface design example explained in this document is targeted for an Microsemi IGLOO device. Figure 1 shows a diagram of the mobile SDRAM interface. The design uses Microsemi's Core8051 embedded controller and generates the required control signal to interface with the mobile SDRAM.

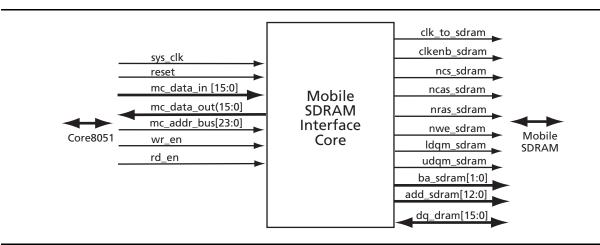


Figure 1 • Mobile SDRAM Core Interface Diagram



# **Interface Description**

The interface details of the IP are given in Table 1.

### Table 1 • Interface Description

Port	Direction	Description			
sys_clk	Input	System clock of 20 MHz			
clk_to_sdram	Output	Mobile SDRAM clock 20 MHz			
clkenb_sdram	Output	Clock enable (active High)			
reset	Input	System reset (active Low)			
rd_en_in	Input	Read enable (active High)			
wr_en_in	Input	Write enable (active High)			
mc_data_in[15:0]	Input	Write data for interface block			
mc_data_out[15:0]	Output	Read back data from interface block			
mc_addr_bus[23:0]	Input	Address bus			
dq_sdram[15:0]	Bidirectional	Mobile SDRAM data bus			
add_sdram[12:0]	Output	Mobile SDRAM address bus			
ba_sdram[1:0]	Output	Bank address			
ldqm_ sdram	Output	Lower data byte mask (active High)			
udqm_ sdram	Output	Upper data byte mask (active High)			
nwe_sdram	Output	Write enable for Mobile SDRAM (active Low)			
nras_sdram	Output	Mobile SDRAM RAS (active Low)			
ncas_sdram	Output	Mobile SDRAM CAS (active Low)			
ncs_sdram	Output	Mobile SDRAM chip select (active Low)			

## **Utilization Details**

This design can be implemented in Microsemi AGL250 or A3P250 devices. However, for testing purposes, this design was verified using Microsemi's AGL600V2-484 FBGA IGLOO device. Table 2 gives the utilization details for AGL600V2-484 FBGA, which include mobile SDRAM interface, Core8051, and glue logic.

Resource	Used	Total	Percentage
Core	5,972	13,824	43.20%
I/O (with clocks)	42	235	17.87%
Differential I/Os	0	60	0.00%
Global (chip+quadrant)	4	18	22.22%
PLL	1	1	100.005
RAM/FIFO	11	24	45.83%
Low static I <sub>CC</sub>	0	1	0.00%
FlashROM	0	1	0.00%
User JTAG	1	1	100.00%



# **Testing Scheme**

For testing purposes, the mobile SDRAM interface design example is instantiated in a top level-file, as shown in Figure 2. The hardware verification of this design is done on Microsemi's IGLOO Development Kit, along with a customized daughter board, using Micron Mobile SDRAM (MT48LC8M16LFB4-75M). Mobile SDRAM was verified for erase, read, and write operation using the FS2 debugger and the software executable.

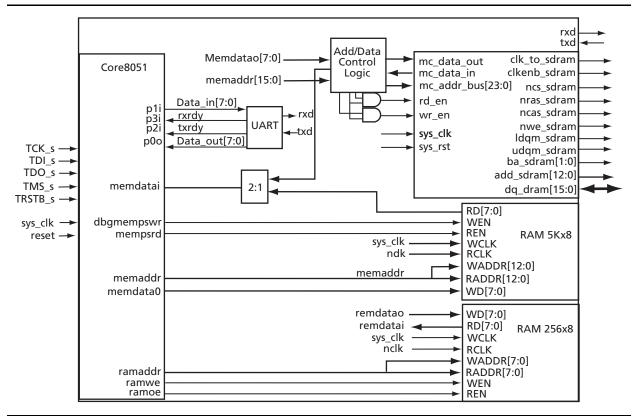


Figure 2 • Test Setup for Mobile SDRAM Interface

## **Software Interface and Design details**

The software modules consist of two applications that test and verify the working of the mobile SDRAM interface.

- 1. Application software: This software is written in C language under the Windows<sup>®</sup> platform and runs on PC, which is interfaced to the Microsemi board through a USB port. The program uses a command prompt user interface to perform write and read operations on the mobile SDRAM and verify that the read data is correct.
- Firmware software: This software is written in C language and must be initially downloaded to the Program Memory of Core8051. This program can be used for Write and Read operations with the Mobile SDRAM memory.

The offset addresses corresponding to various registers are hardcoded in the code. Read and write operations are performed on a Bank basis. Each bank can be individually read or written sequentially. Each Bank consists of four MBytes. Before performing any operation, status signal Ready/Busy is verified. Table 3 shows the register mapping.

Address	Register Name	R/W	Description
0x0000	BASEADDRESS		Base address of the design example

The set of software files used for testing the IP is provided in the software folder.



## **Software Files**

### Firmware Files

### Main.c

This file contains source code for the SDRAM drivers. The code handles the command for UART communication and performs the read and write operations on the RAM device.

### **Application Files**

### Main.c

This file provides the main functionality of the program. The user interaction, data validation, and communication with the USB port are done inside this file. User input is validated and sent to the USB port sequentially.

### UsbCom.c

This source file takes care of the USB communication.

### Program Execution (SDRam.exe)

The executable program is run from a Windows environment. When the program is run, the menu options are displayed. The option for communication port is selected based on the USB port where the board is connected. The option for Read, Write, or verify is displayed following that. Make sure you program the device and load the hex file before running the executable.

When the application program SDRam.exe is executed (SDRam.exe is provided with the design example), the screen shown in Figure 3 appears on the laptop or PC monitor.

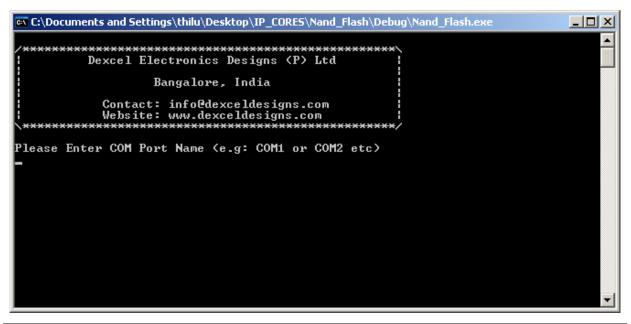
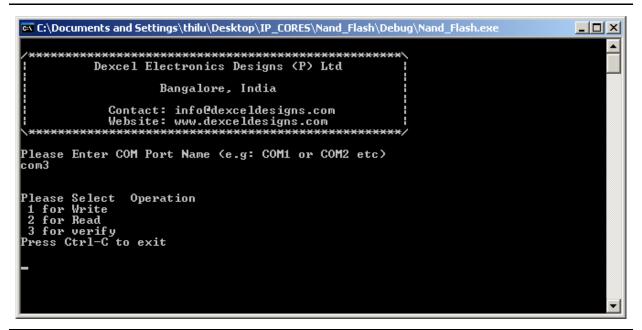


Figure 3 • COM Port Identification

Enter the COM port name. You can find the COM port in Device Manager (in this example it is COM3).



After you specify the COM port, the screen shown in Figure 4 appears.



#### Figure 4 • Selecting an Operation

The options are 1 for Write, 2 for Read, and 3 for verify. For testing each bank, follow the sequence of Write, Read, verify. First select 1 for a Write operation. The screen shown in Figure 5 appears.

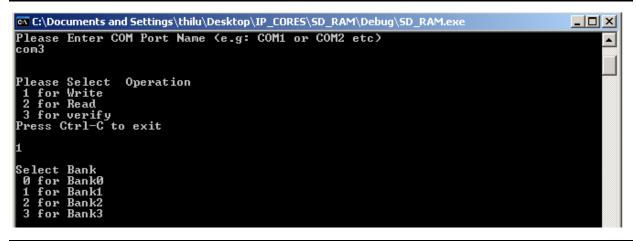


Figure 5 • Selection of Bank

Select each bank, 0 to 3, one at a time, to perform the test on that particular bank.



When you select a bank, the screen shown in Figure 6 appears.

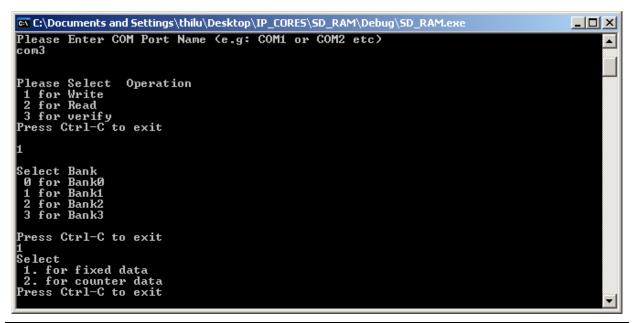


Figure 6 • Selection of Data Type

Select 1 for filling a SDRAM location with fixed data. Select 2 for selecting an incremental counter value from 0x0000 to 0xFFFF.

If option 1 is selected, the screen shown in Figure 7 appears.

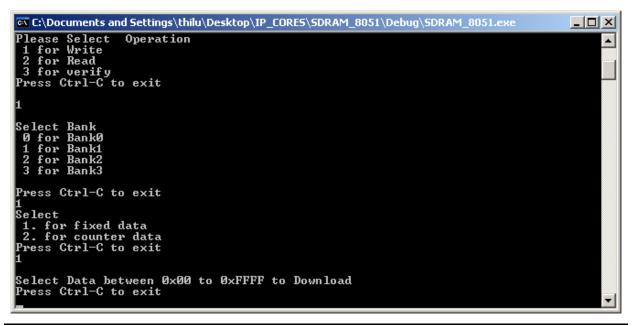


Figure 7 • Selection of Data

Select a data value from 0x00 to 0xFFFF.



During the write operation, a status message appears on the screen: "Writing Data please wait." (Figure 8). The writing process takes a few minutes to complete. A temporary file, WRITE\_DATA.txt, is created for the type of data selected. This file is used later during the verification process.

C:\Documents and Settings\thilu\Desktop\IP_CORES\SDRAM_8051\Debug\SDRAM_8051.exe	
1	
Select Bank O for BankO	
1 for Bank1 2 for Bank2	
3 for Bank3	
Press Ctrl-C to exit	
Select 1. for fixed data	
2. for counter data Press Ctrl-C to exit 1	
Select Data between 0x00 to 0xFFFF to Download Press Ctrl-C to exit 0x01	
Uniting Data places whit	
Writing Data please wait	

### Figure 8 • Status Message while Writing

After completion of the write operation, a window indicating, "WRITE COMPLETED" appears, as shown in Figure 9.

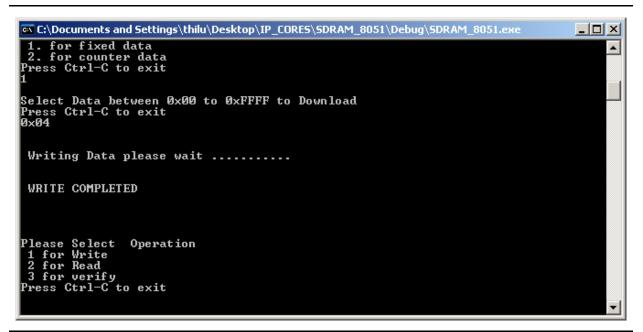
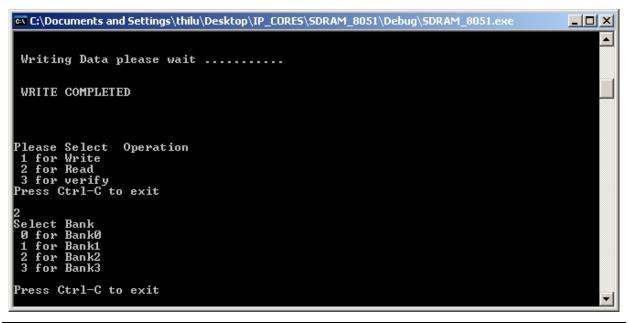


Figure 9 • Status Message for Write Completion

After the write operation finishes, the selection menu appears again and you can select option 2 for a read operation.



When Read is selected, the screen shown in Figure 10 appears.



#### Figure 10 • Read Operation Selection

Select the bank number to read.

After the bank is selected, a status message, "Reading Data please wait," appears on the screen (Figure 11). The reading process may take a few minutes more than write, since the read data must be transferred using a slower UART interface. The read data is stored in a temporary file, READ\_DATA.txt.

🔤 C:\Documents and Settings\thilu\Desktop\IP_CORES\SDRAM_8051\Debug\SDRAM_8051.exe	
Please Select Operation	
2 for Read 3 for verify Bused Ctal Cate suit	
Press Ctrl-C to exit	
Z Select Bank Ø for BankØ	
1 for Bank1 2 for Bank2	
3 for Bank3	
Press Ctrl-C to exit 1	
Reading Data please wait	
	-

### Figure 11 • Status Message for Read Operation



After completion of the read operation, the screen shown in Figure 12 appears.

🛋 c:\Documents and Settings\thilu\Desktop\Ip_cores\Sdram_8051\Debug\SDRAM_8051.exe	
Select Bank Ø for BankØ 1 for Bank1 2 for Bank2 3 for Bank3	
Press Ctrl-C to exit 1	
Reading Data please wait	
READ DATA COMPLETED	
Please Select Operation 1 for Write 2 for Read 3 for verify Press Ctrl-C to exit	×

#### Figure 12 • Status Message after Read Operation

To verify whether the data written and read were correct, select 3 for verification. The Verify command compares an immediately read value with the last written data. A message appears (Figure 13), detailing the results of the verification process

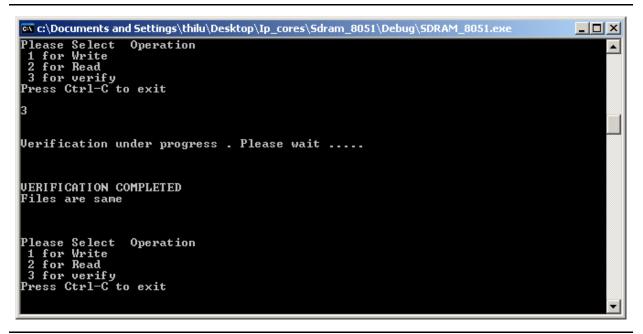


Figure 13 • Verification Status Message

Note: During a write operation, a text file named Write\_Data.txt is created in the path from which SDRAM.exe was executed. Similarly, during a read operation, Read\_Data.txt is created. These files are overwritten by a new operation. During verification, these two files are compared and the result is displayed. In this process, the immediately read data content and the last written data content are compared. Hence for valid testing, a write and



read must be performed for the same bank; otherwise the result obtained would not be correct, because the data written to one bank and read from another bank might not be the same.

# **Timing Diagram**

The simulation waveforms are shown in Figure 14 and Figure 15 on page 11.

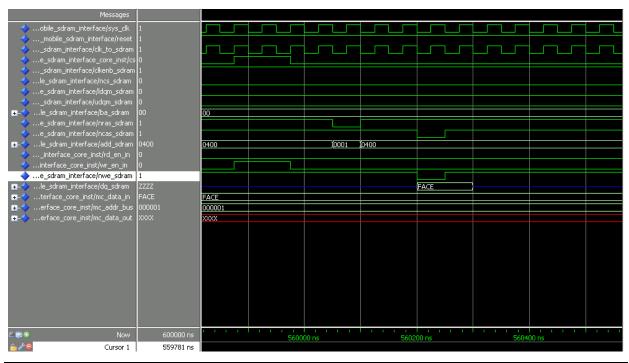


Figure 14 • Write Cycle

Figure 14 gives the Write Cycle on mobile SDRAM. It shows the data being written is 0xFACE on location 0x0001 of the mobile SDRAM.



Messages									
obile_sdram_interface/sys_clk	1								إكلاكاك
mobile_sdram_interface/reset	1								
2sdram_interface/clk_to_sdram	1								
e_sdram_interface_core_inst/cs									
sdram_interface/clkenb_sdram	1								
2 le_sdram_interface/ncs_sdram	0								
2e_sdram_interface/ldqm_sdram	0								
	0								
	00	00							
e_sdram_interface/nras_sdram	1								
e_sdram_interface/ncas_sdram	1								
	0400	0400	0001	0400					
interface_core_inst/rd_en_in	1								
interface_core_inst/wr_en_in	0								
e_sdram_interface/nwe_sdram	ı ZZZZ						<u> </u>		
	FACD					FACE			
+		FACD				)FAC	2		
erface_core_inst/mc_addr_bus		000001							
	FACD	FACD							
🛎 📰 💿 👘 Now	600000 ns	58480	1111		000 ns	- 	00 ns	5854	
Cursor 1	584733 ns	56460	JUTIS	505	000 TIS	5052	00 115	5054	JUTIS
Culsor 1	1 3347331IS								

Figure 15 • Read Cycle

## **Application Area**

Mobile SDRAM is used in almost all compact handhelds, due largely to its compact size and low-power architecture. While the majority of the volume applications are found in the consumer market segment, the portable market for industrial and military applications is growing at a rapid pace.

## Conclusion

Mobile SDRAMs provide many benefits for low-power applications, such as mobile phones, handheld media players, cameras, book readers, and other portable applications. Combining Mobile SDRAM with Microsemi's low-power FPGAs provides a high-value solution for power- and cost-sensitive mobile applications.



# List of Changes

The following table lists critical changes that were made in each revision of the document.

Revision	Changes	Page
Revision 1 (March 2015)	Non-Technical Updates.	N/A
Revision 0 (June 2009)	Initial Release.	N/A



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